

INTEGRATED SEMICONDUCTOR FIN DEVICE AND A METHOD FOR MANUFACTURING SUCH DEVICE

Abstract of the Disclosure

A CMOS circuit for and method of forming a FinFET device is disclosed. The method includes providing a substrate comprising a semiconductor layer, forming on the semiconductor layer active areas insulated from each other by field areas, forming at least one dummy gate on at least one of said active areas and forming source and drain regions on the at least one of the active areas. The method also includes covering the substrate with an insulating layer leaving said dummy gate exposed and forming an open cavity by patterning the dummy gate to form a dummy fin and a semiconductor fin aligned to said dummy fin, both fins extending from the source to the drain regions.

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